

www.vishay.com

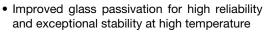
Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 25 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	25 A			
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V 1200 V			
V _{TM}	1.70 V			
I _{GT}	60 mA			
T _J	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

FEATURES





• High dl/dt and dV/dt capabilities

- Standard package
- Low thermal resistance
- Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
L		25	Α				
I _{T(AV)}	T _C	85	°C				
I _{T(RMS)}		40	А				
I _{TSM}	50 Hz	420	Α				
	60 Hz	440					
2t	50 Hz	867	A2-				
1-1	60 Hz	790	A ² s				
V _{DRM} /V _{RRM}		100 to 1200	V				
tq	Typical	110	μs				
T _J		-65 to +125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT } T_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-25RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

Notes

- (1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs
- (2) For voltage pulses with $t_p \le 5$ ms



ABSOLUTE MAXIMUM RAT	INGS					
PARAMETER	SYMBOL		TEST COND	DITIONS	VALUES	UNITS
Maximum average on-state current		190° oinuosi	180° sinusoidal conduction		25	Α
at case temperature	I _{T(AV)}	100 51110501	dai conduction		85	°C
Maximum RMS on-state current	I _{T(RMS)}				40	Α
		t = 10 ms	No voltage		420	
Maximum peak, one-cycle	<u></u>	t = 8.3 ms	reapplied		440	Α
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		350	A
	t = 8.3 ms reapplied Sinusoidal half wave,	370				
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	867	- A ² s
		t = 8.3 ms	reapplied		790	
		t = 10 ms	100 % V _{RRM} reapplied		615	
		t = 8.3 ms			560	
Maximum I ² √t for fusing	l²√t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		8670	A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		0.99	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		1.40	V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		10.1	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		5.7	1115.2	
Maximum on-state voltage	V _{TM}	I _{pk} = 79 A, T _J = 25 °C		1.70	V	
Maximum holding current	I _H	T 0500		/ registive load	130	mA
Latching current	IL	1,1=25 0,8	$T_J = 25$ °C, anode supply 6 V, resistive load		200	IIIA

SWITCHING							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
	$V_{DRM} \le 600 \text{ V}$					200	
Maximum rate of rise	e $V_{DRM} \le 800 \text{ V}$ $T_J = T_J \text{ maximum, } V_{DM} = \text{Rated } V_{DRM}$ $dI/dt \qquad Gate \text{ pulse} = 20 \text{ V. } 15 \Omega. t_0 = 6 \text{ us. } t_r = 6 \text{ vs. }$		$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ Gate pulse = 20 V, 15 Ω , $t_p = 6 \mu s$, $t_r = 0.1 \mu s$ maximum	180	A/µs		
of turned-on current $V_{DRM} \le 10$	$V_{DRM} \leq 1000 \; V$	di/dt	$I_{TM} = (2 \text{ x rated dI/dt}) \text{ A}$	160	Ανμο		
V _{DRM} ≤ 160			,,	150			
Typical turn-on time		t _{gt}	$T_J = 25$ °C, at rated V_{DRM}/V_{RRM} , $T_J = 125$ °C	0.9			
Typical reverse recovery time		t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \ \mu s$, $dI/dt = -10 \ A/\mu s$	4	μs		
Typical turn-off time		tq	$\begin{split} T_J &= T_J \text{ maximum, } I_{TM} = I_{T(AV)}, t_p > 200 \mu\text{s, } V_R = 100 \text{ V}, \\ dI/dt &= \text{-} 10 \text{ A/}\mu\text{s, } dV/dt = 20 \text{ V/}\mu\text{s linear to 67 } \% \text{ V}_{DRM}, \\ \text{gate bias 0 V to 100 W} \end{split}$	110	μο		

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs	
of off-state voltage	uv/at	T _J = T _J maximum linear to 67 % rated V _{DRM}	300 ⁽¹⁾	v/μS	

Note

 $^{^{(1)}}$ Available with: $dV/dt = 1000 \text{ V/}\mu\text{s}$, to complete code add S90 i.e. 25RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}	T T		8.0	w
Maximum average gate power	P _{G(AV)}	I j = I j maximum	$T_J = T_J$ maximum		
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	А
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
		T _J = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C		60	
		T _J = 125 °C		35	
	V _{GT}	T _J = - 65 °C		3.0	V
DC gate voltage required to trigger		T _J = 25 °C		2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	$T_J = T_J$ maximum, $V_{DRM} = Rated value$		2.0	mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to +125	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation		K/W	
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased	0.35	rv vv	
Allowable mounting toward		Non-lubricated threads	3.4 ^{+ 0 - 10} % (30)	N⋅m	
Allowable mounting torque		Lubricated threads	2.3 ^{+ 0 - 10} % (20)	(lbf · in)	
Approximate weight			14	g	
Approximate weight			0.49	oz.	
Case style		See dimensions - link at the end of datasheet TO-48 (TO-		-208AA)	

△R _{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.17	0.13		
120°	0.21	0.22		
90°	0.27	0.30	$T_J = T_J$ maximum	K/W
60°	0.40	0.42		
30°	0.69	0.70		

Note

The table above shows the increment of thermal resistance R_{th,JC} when devices operate at different conduction angles than DC

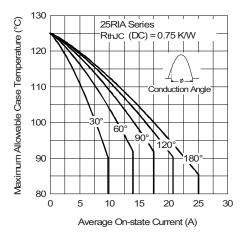


Fig. 1 - Current Ratings Characteristics

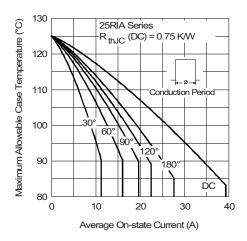


Fig. 1 - Current Ratings Characteristics

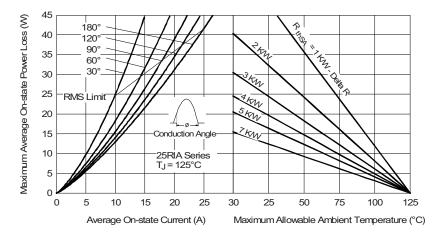


Fig. 2 - On-State Power Loss Characteristics

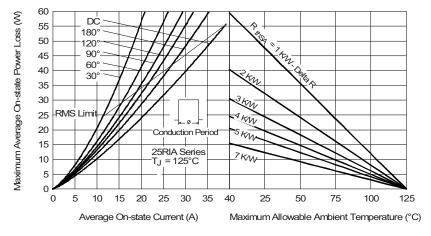


Fig. 3 - On-State Power Loss Characteristics

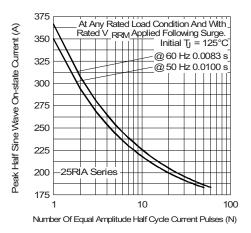


Fig. 4 - Maximum Non-Repetitive Surge Current

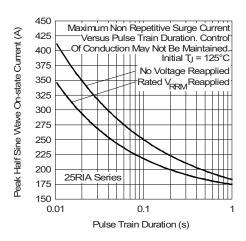


Fig. 5 - Maximum Non-Repetitive Surge Current

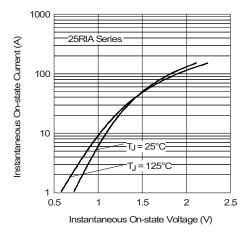


Fig. 6 - Forward Voltage Drop Characteristics

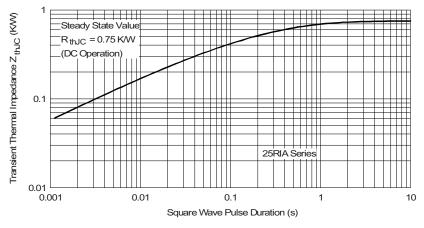


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics

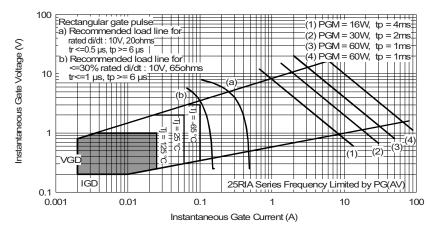
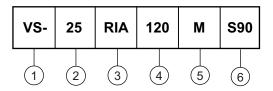


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



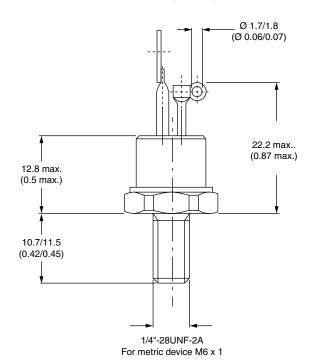
- Vishay Semiconductors product
- 2 Current code
- 3 Essential part number
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A
 M = stud base TO-48 (TO-208AA) M6 x 1
- 6 Critical dV/dt:
 None = 300 V/µs (standard value)
 S90 = 1000 V/µs (special selection)

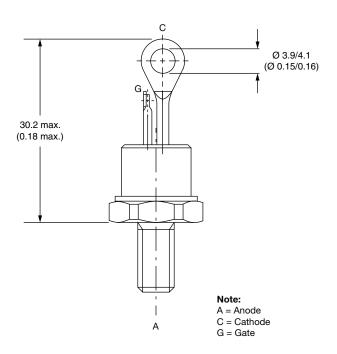
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95333		

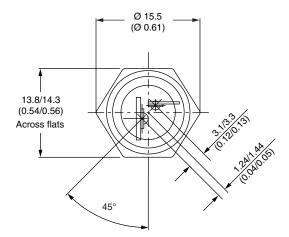


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.